

# isc N-Channel MOSFET Transistor

# BUK573-100A/B

#### **DESCRIPTION**

- Drain Source Voltage
  - : V<sub>DSS</sub>= 100V(Min)
- Low R<sub>DS(ON)</sub>
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



#### **APPLICATIONS**

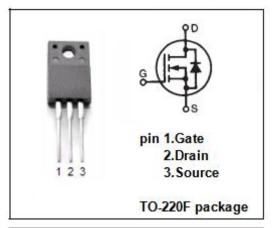
 Designed for Switched Mode Power Supplies (SMPS), motor control,welding, and in general purpose switching resistance applications

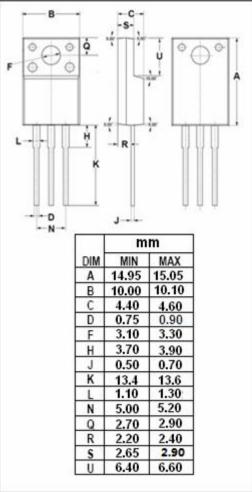
## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

ARAMETER		VALUE	UNIT
Drain-Source Voltage (V <sub>GS</sub> =0)		100	V
Gate-Source Voltage		±15	V
Drain Current-continuou s@ TC=25°C	BUK573-100A	8.3	А
	BUK573-100B	7.5	
Total Dissipation@TC=25℃		25	W
Max. Operating Junction Temperature		150	$^{\circ}$ C
Storage Temperature Range		-55-150	$^{\circ}$
	Drain-Source Voltage  Gate-Source Voltage  Drain  Current-continuou  s@ TC=25°C  Total Dissipation@T  Max. Operating Jun	Drain-Source Voltage  Drain Current-continuous@TC=25°C  Max. Operating Junction Temperature	Drain-Source Voltage ( $V_{GS}$ =0) 100  Gate-Source Voltage $\pm$ 15  Drain Current-continuou $\pm$ 0 BUK573-100A 8.3  RUK573-100B 7.5  Total Dissipation@TC=25°C 25  Max. Operating Junction Temperature 150

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	5	°C/W





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## BUK572-100A/B

### **ELECTRICAL CHARACTERISTICS (Tc=25°C)**

SYMBOL	PARAMETER	CONDITIONS		MIN	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 0.25mA		100		V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = 1.0mA		1.0	2.0	V
R <sub>DS(on)</sub>	Drain-Source On-stage Resistance	V <sub>GS</sub> = 5V; I <sub>D</sub> = 5A	BUK573-100A		0.18	Ω
			BUK573-100B	-	0.22	Ω
lgss	Gate Source Leakage Current	$V_{GS}$ = $\pm 15V$ ; $V_{DS}$ = 0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 100V; V <sub>GS</sub> = 0		1	10	uA
V <sub>SD</sub>	Forward On-Voltage	I <sub>S</sub> = 8.3A; V <sub>GS</sub> = 0			1.3	V

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